## NSN 5961-01-168-3350

A110a0

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-168-3350 **Inclosure Material:** Metal **Overall Length:** 1.328 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-64 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 800.0 repetitive peak off-state voltage and 800.0 repetitive peak reverse voltage and 900.0 nonrepetitive peak off-state voltage **Current Rating Per Characteristic:** 35.00 amperes forward current, total rms nanoamperes **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: